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Kind regards,

Team Nexperia



# PSMN1R5-40ES

N-channel 40 V 1.6 mΩ standard level MOSFET in I2PAK.

Rev. 01 — 19 April 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in I2PAK (SOT226) package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC convertors
- Motor control
- Load switching
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	40	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>	[1]	-	120	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	338	W
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 13</a>	[2]	1.3	1.6	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}$ ; $I_D = 75\text{ A}$ ;	-	32	-	nC
$Q_{G(tot)}$	total gate charge	$V_{DS} = 20\text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	136	-	nC

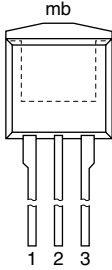
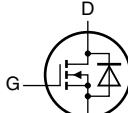
[1] Continuous current is limited by package

[2] Measured 3 mm from package.



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	drain		

SOT226 (I2PAK)

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R5-40ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	40	V	
$V_{DGR}$	drain-gate voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	40	V	
$V_{GS}$	gate-source voltage		-20	20	V	
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C}$	[1]	-	120	A
		$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ see <a href="#">Figure 1</a>	[1]	-	120	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}; T_{mb} = 25\text{ °C};$ see <a href="#">Figure 3</a>	-	1301	A	
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	338	W	
$T_{stg}$	storage temperature		-55	175	°C	
$T_j$	junction temperature		-55	175	°C	
$T_{sld(M)}$	peak soldering temperature		-	260	°C	

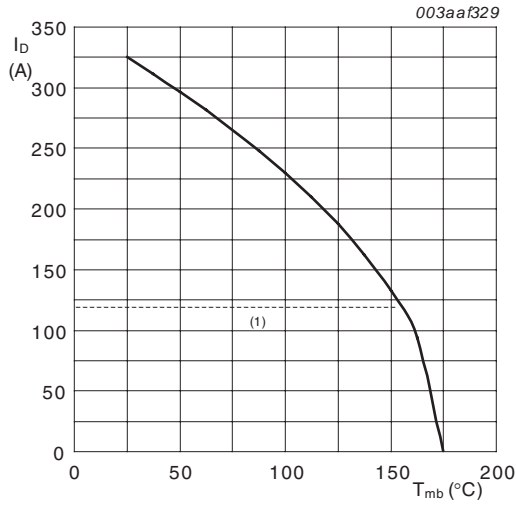
### Source-drain diode

$I_S$	source current	$T_{mb} = 25\text{ °C}$	[1]	-	120	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}; T_{mb} = 25\text{ °C}$	-	-	1301	A

### Avalanche ruggedness

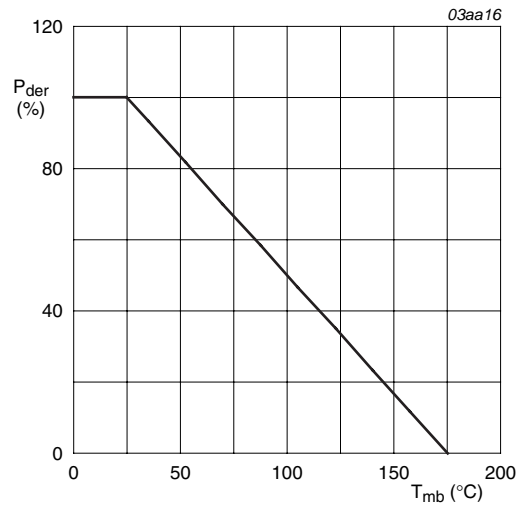
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C}; I_D = 120\text{ A}; V_{sup} \leq 40\text{ V};$ unclamped; $R_{GS} = 50\text{ }\Omega;$ $t_p = 0.1\text{ ms}$	-	-	1.4	J
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[1] Continuous current is limited by package.



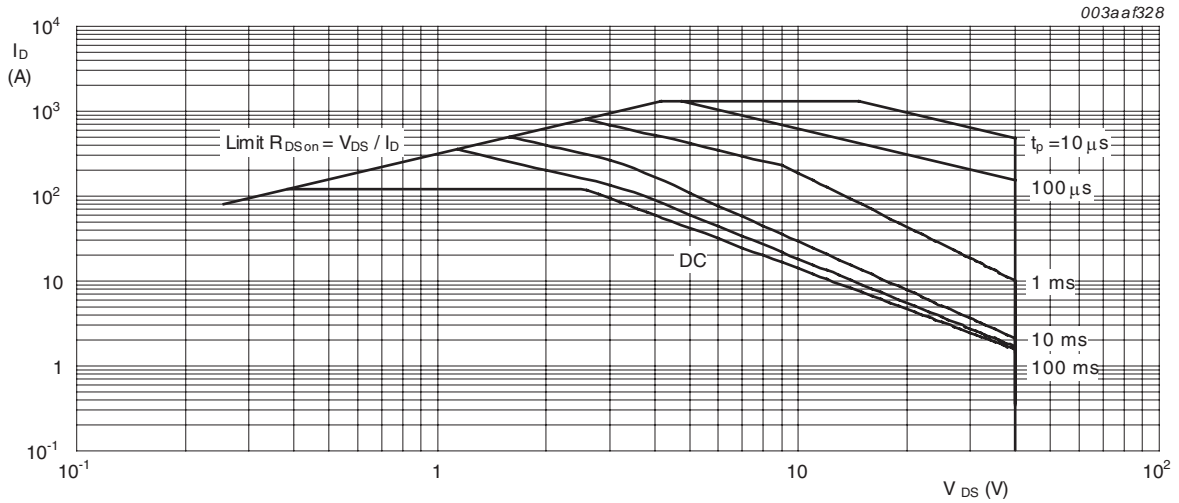
$V_{GS} \geq 10$  V(1) Capped at 120 A due to package

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100 \%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25$  °C;  $I_{DM}$  is a single pulse; Capped at 120 A due to package

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	0.22	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

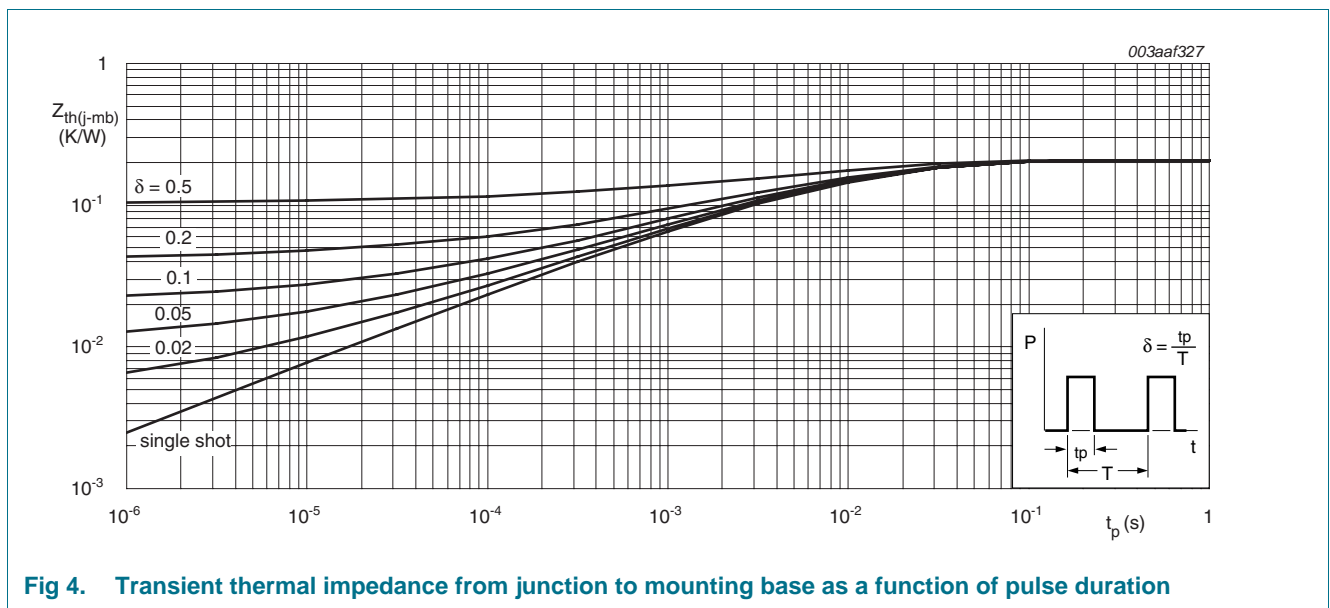


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

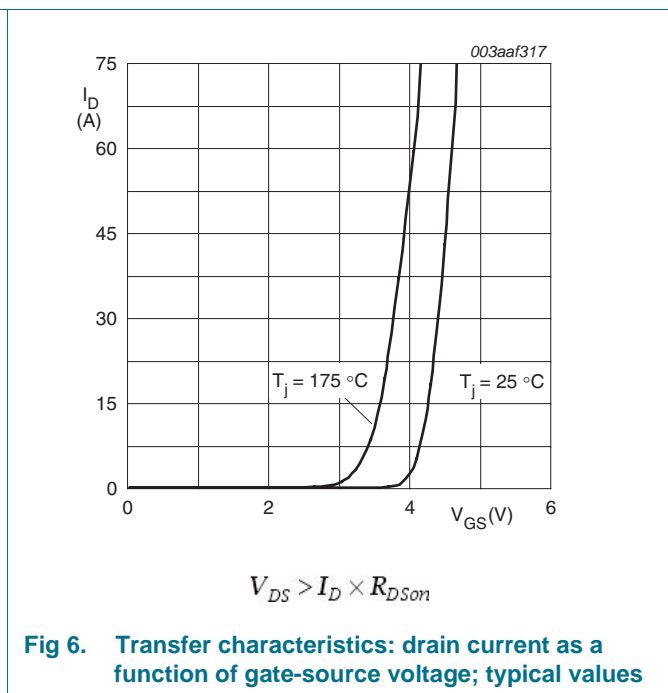
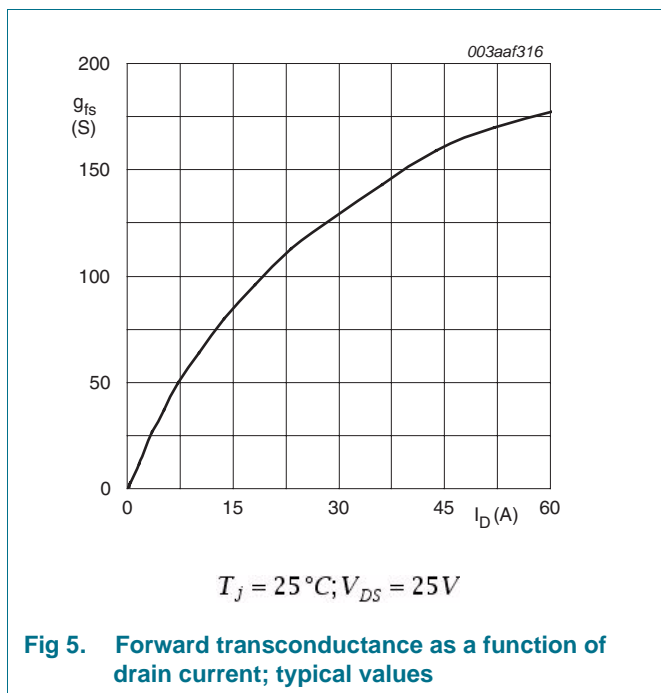
Table 6. Characteristics

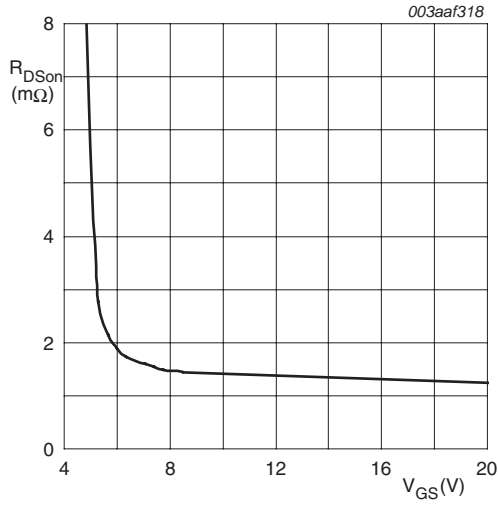
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	36	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	40	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$ ; see <a href="#">Figure 10</a>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C$ ; see <a href="#">Figure 10</a>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 11</a> ; see <a href="#">Figure 10</a>	2	3	4	V
$I_{DSS}$	drain leakage current	$V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.02	10	$\mu A$
		$V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	250	500	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{Dson}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 25 A; T_j = 100 \text{ }^\circ C$ ; see <a href="#">Figure 12</a>	-	1.9	2.3	mΩ
		$V_{GS} = 10 V; I_D = 25 A; T_j = 175 \text{ }^\circ C$ ; see <a href="#">Figure 12</a>	-	2.6	3.2	mΩ
		$V_{GS} = 10 V; I_D = 25 A; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 13</a>	<a href="#">11</a>	-	1.3	1.6
$R_G$	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	1.1	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	133	-	nC
		$I_D = 75 A; V_{DS} = 20 V; V_{GS} = 10 V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	136	-	nC
$Q_{GS}$	gate-source charge		-	52	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	30	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	22	-	nC
$Q_{GD}$	gate-drain charge		-	32	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 20 V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	6.1	-	V
$C_{iss}$	input capacitance	$V_{DS} = 20 V; V_{GS} = 0 V; f = 1 \text{ MHz}$ ;	-	9710	-	pF
$C_{oss}$	output capacitance	$T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 16</a>	-	2042	-	pF
$C_{riss}$	reverse transfer capacitance		-	994	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 20 V; R_L = 0.8 \text{ } \Omega; V_{GS} = 10 V$ ;	-	45	-	ns
$t_r$	rise time	$R_{G(ext)} = 4.7 \text{ } \Omega$	-	66	-	ns
$t_{d(off)}$	turn-off delay time		-	111	-	ns
$t_f$	fall time		-	53	-	ns

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 17</a>	-	0.8	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$	-	64	-	ns
$Q_r$	recovered charge	$I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; $T_j = 25\text{ °C}$	-	117	-	nC

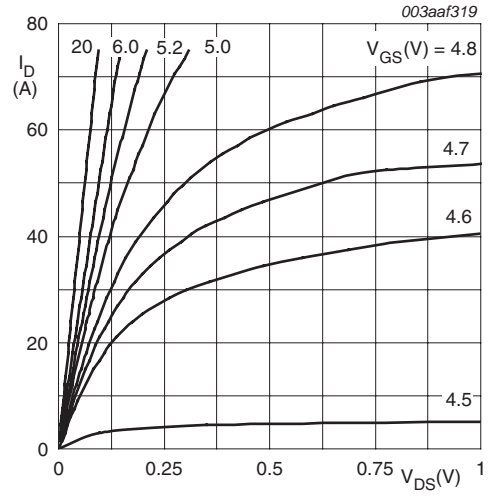
[1] Measured 3 mm from package.





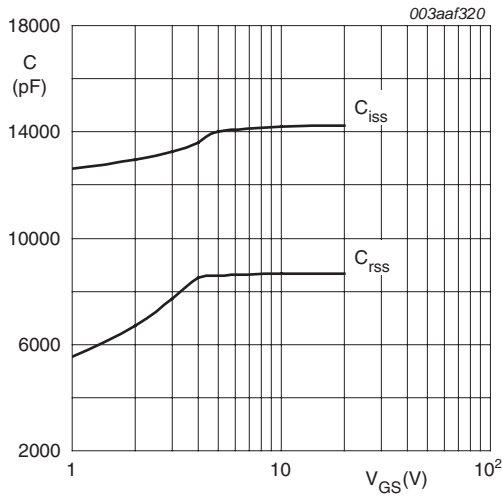
$T_j = 25^\circ\text{C}; V_{DS} = 25\text{V}$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values.



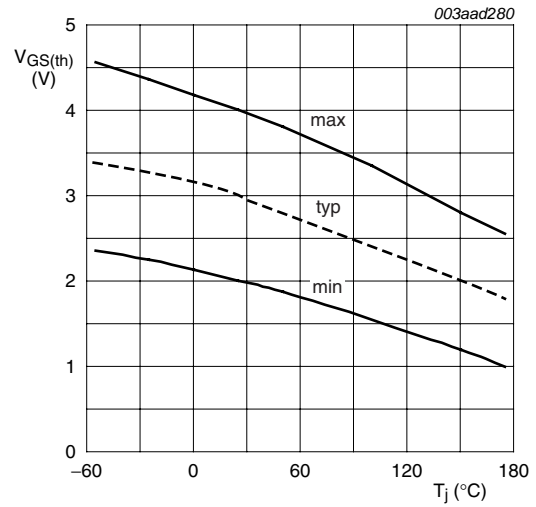
$T_j = 25^\circ\text{C}$

Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values



$V_{DS} = 0\text{V}; f = 1\text{MHz}$

Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



$I_D = 1\text{mA}; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature



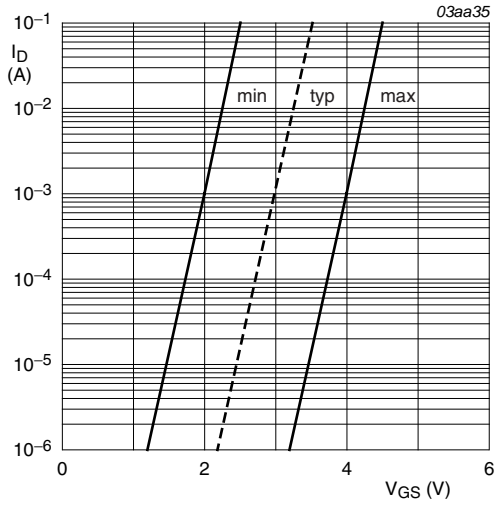


Fig 11. Sub-threshold drain current as a function of gate-source voltage

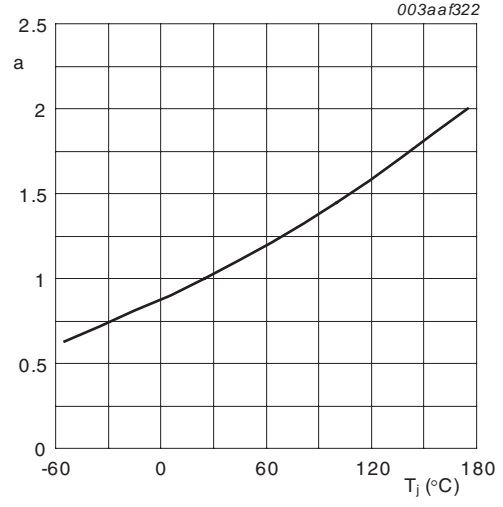


Fig 12. Normalized drain-source on state resistance factor as a function of junction temperature

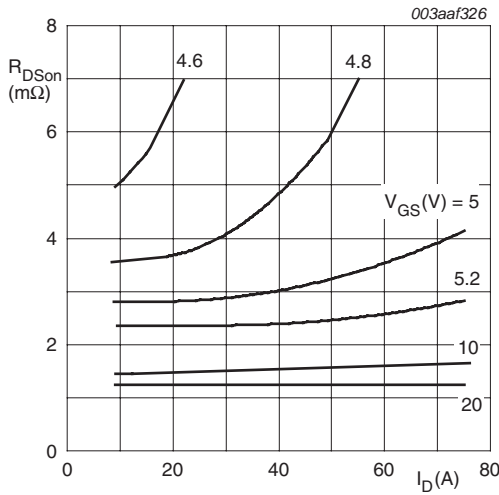


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

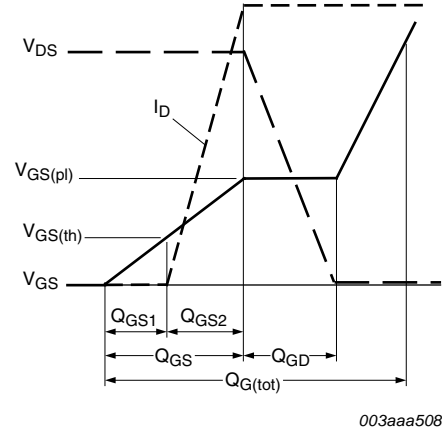
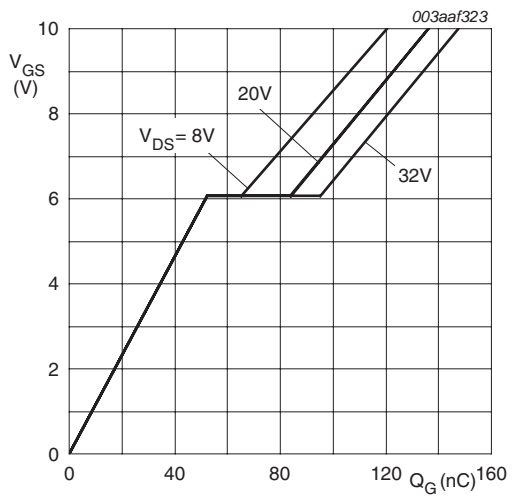
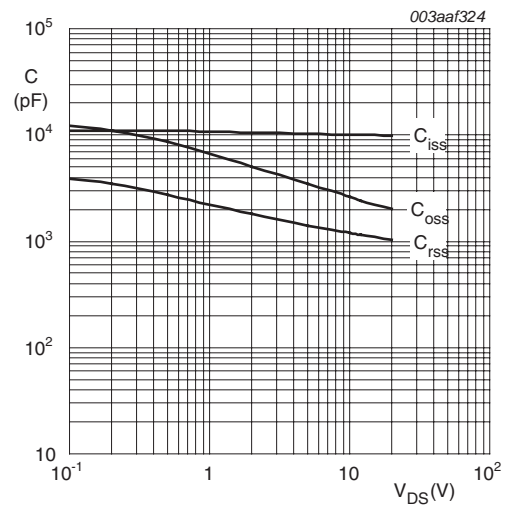


Fig 14. Gate charge waveform definitions



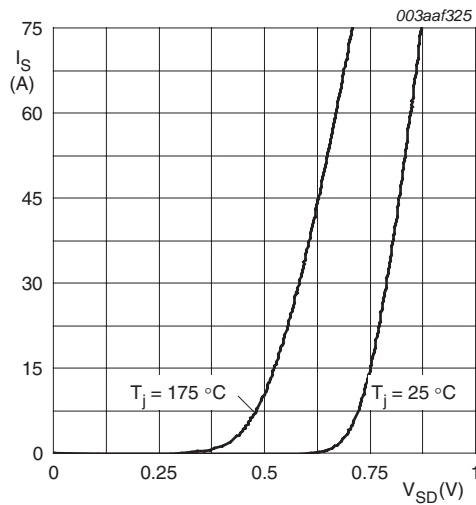
$I_D = 75 A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0V$

Fig 17. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended package (I2PAK); low-profile 3-lead TO-262

SOT226

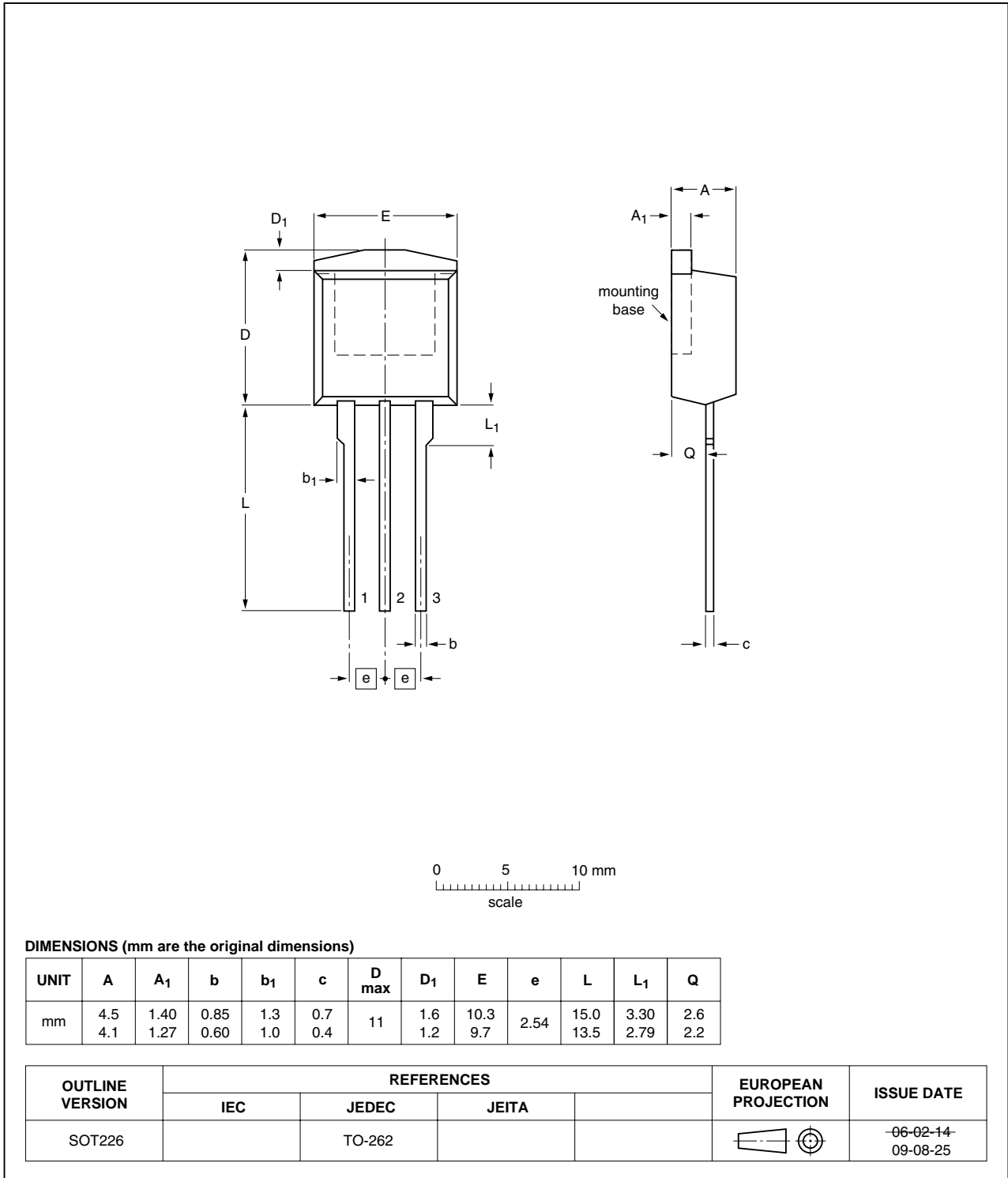


Fig 18. Package outline SOT226 (I2PAK)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R5-40ES v.1	20110419	Product data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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